

# ELECTRONIC INFORMATION DISCLOSURE STATEMENT

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Title of Invention	METHOD FOR FABRICATING A NITRIDED SILICON-OXIDE GATE DIELECTRIC
Application Number :	10/604905
Confirmation Number:	8-26-03
First Named Applicant:	Jay Burnham
Attorney Docket Number:	BUR920020109US1
Art Unit:	2813
Examiner:	
Search string:	( 6399445 or 6380056 or 6368923 or 6335252 or 6291867 or 6200651 or 6114258 or 6136654 or 6171911 or 6027977 or 5726087 or 5648284 or 5596218 or 5445999 or 5219773 or 4621277 ).pn

## US Patent Documents

Note: Applicant is not required to submit a paper copy of cited US Patent Documents

init	Cite.No.	Patent No.	Date	Patentee	Kind	Class	Subclass
R	1	6399445	2002-06-04	Hattangady et al			
	2	6380056	2002-04-30	Shue et al			
	3	6368923	2002-04-09	Huang			
	4	6335252	2002-01-01	Oishi et al			
	5	6291867	2001-09-18	Wallace et al			
	6	6200651	2001-03-13	Roche et al			
	7	6114258	2000-09-05	Miner et al			
	8	6136654	2000-10-24	Kraft et al			
	9	6171911	2001-01-09	Yu			
	10	6027977	2000-02-22	Mogami			
	11	5726087	1998-03-10	Tseng et al			
	12	5648284	1997-07-15	Kusunoki et al			
	13	5596218	1997-01-21	Soleimani et al			
	14	5445999	1995-08-29	Thakur et al			
	15	5219773	1993-06-15	Dunn			
	16	4621277	1986-11-04	Ito et al			

## Signature

Examiner Name	Date
	10/24/03

INFORMATION DISCLOSURE CITATION (Use several sheets if necessary)			Docket Number (Optional) <b>BUR920020109US1</b>	Application Number <b>10/604905</b>		
			Applicant(s) <b>Burnham et al.</b>			
			Filing Date <b>08/26/03</b>	Group Art Unit <b>2813</b>		
U.S. PATENT DOCUMENTS						
EXAMINER INITIAL	REF	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS
FILING DATE IF APPROPRIATE						
FOREIGN PATENT DOCUMENTS						
REF	DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	Translation
						YES
OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)						
		IBM Technical Disclosure Bulletin, Vol. 28, No. 6, November 1985, CONTROLLED NITRIDATION OF SiO <sub>2</sub> FOR THE FORMATION OF GATE INSULATORS IN FET DEVICES, Merz et al., Pages 2665-2666.				
		IBM Technical Disclosure Bulletin, Vol. 19, No. 4, September 1976, MNOS REACTOR PROCESS, Haggett et al., Page 1160.				
EXAMINER <i>[Signature]</i>			DATE CONSIDERED <i>10/24/05</i>			
EXAMINER: Initial if citation considered, whether or not citation is in conformance with MPEP Section 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.						

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INFORMATION DISCLOSURE CITATION <i>(Use several sheets if necessary.)</i>			Docket Number (Optional) <b>BUR920020109US1</b>		Application Number <b>10/604905</b>	
			Applicant(s) <b>Burnham et al.</b>		Filing Date <b>08/26/03</b>	
<b>U.S. PATENT DOCUMENTS</b>						
<b>*EXAMINER INITIAL</b>	<b>REF</b>	<b>DOCUMENT NUMBER</b>	<b>NAME</b>	<b>CLASS</b>	<b>SUBCLASS</b>	<b>FILED DATE IF APPROPRIATE</b>
<b>FOREIGN PATENT DOCUMENTS</b>						
<b>REF</b>	<b>DOCUMENT NUMBER</b>	<b>DATE</b>	<b>COUNTRY</b>	<b>CLASS</b>	<b>SUBCLASS</b>	<b>Transition</b>
						<b>YES</b>
<b>OTHER DOCUMENTS</b> <i>(Including Author, Title, Date, Pertinent Pages, Etc.)</i>						
		<b>IBM Technical Disclosure Bulletin, Vol. 14, No. 4, September 1971, TRANSCONDUCTANCE IN SILICON GATE NITRIDE-OXIDE IGBT, Dockerty et al., 1 sheet.</b>				
EXAMINER <i>D</i>			DATE CONSIDERED <i>10/24/05</i>			

**EXAMINER:** Initial if citation considered, whether or not citation is in conformance with MPEP Section 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.